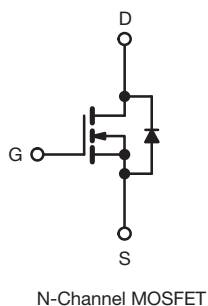


E Series Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	700	
$R_{DS(on)}$ (Ω) typ. at 25 °C	$V_{GS} = 10$ V	0.025
Q_g (nC) max.	591	
Q_{gs} (nC)	84	
Q_{gd} (nC)	160	
Configuration	Single	



FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)

ORDERING INFORMATION

Package	Super-247
Lead (Pb)-free	SiHS90N65E-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	323	
Linear Derating Factor		5	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	1930	mJ
Maximum Power Dissipation	P_D	625	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	dV/dt	$T_J = 125$ °C	V/ns
Reverse Diode dV/dt ^d			
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C


Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 140$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 11.7$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

**THERMAL RESISTANCE RATINGS**

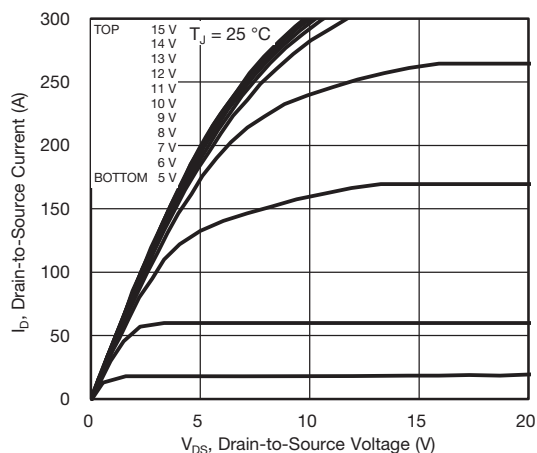
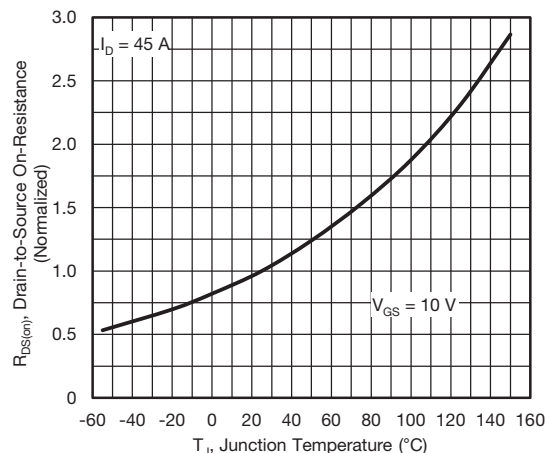
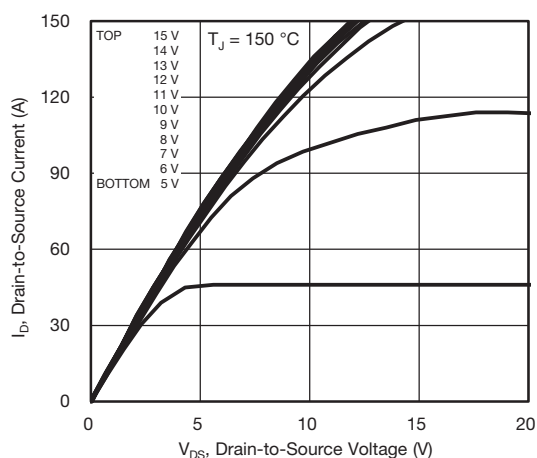
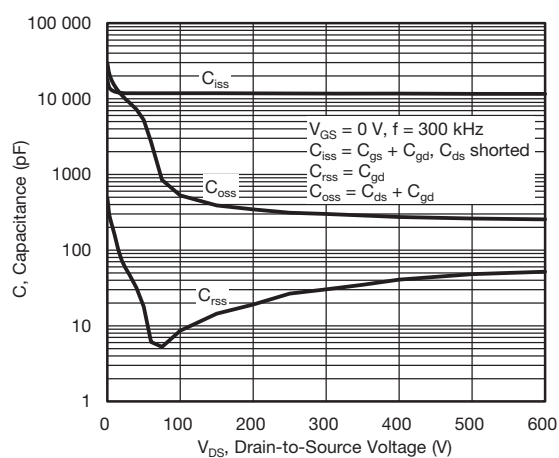
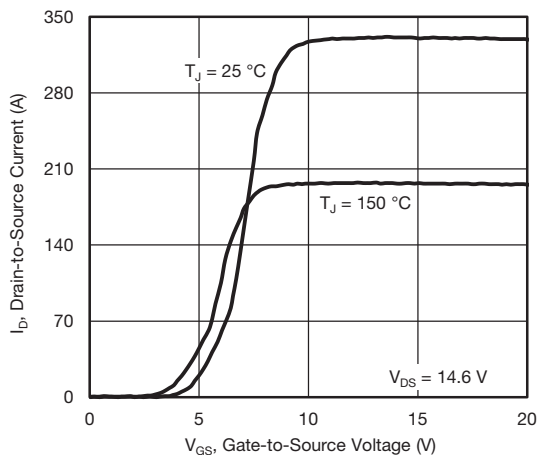
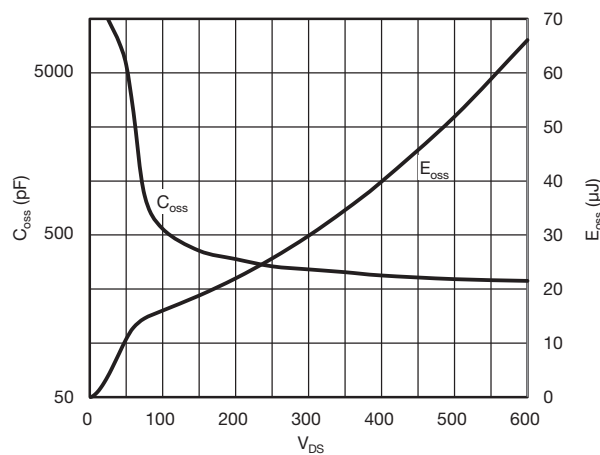
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.2	

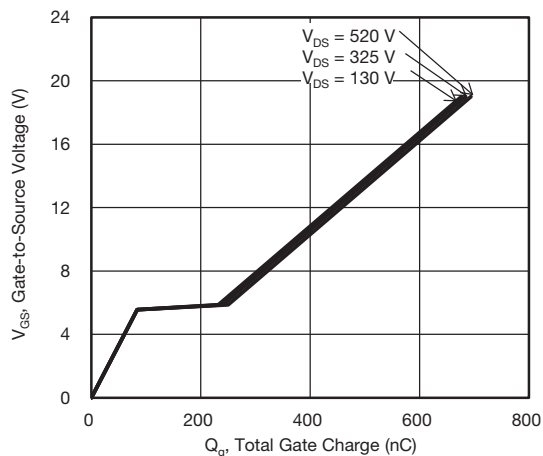
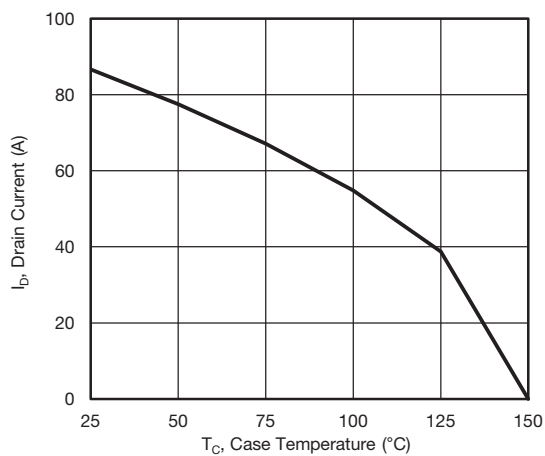
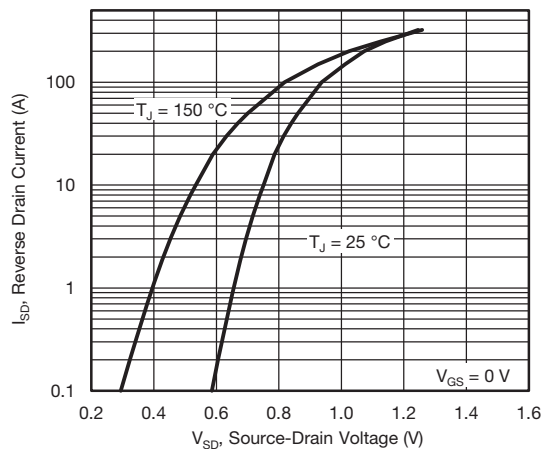
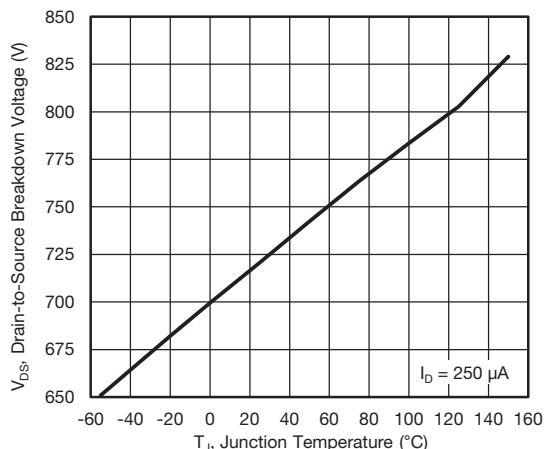
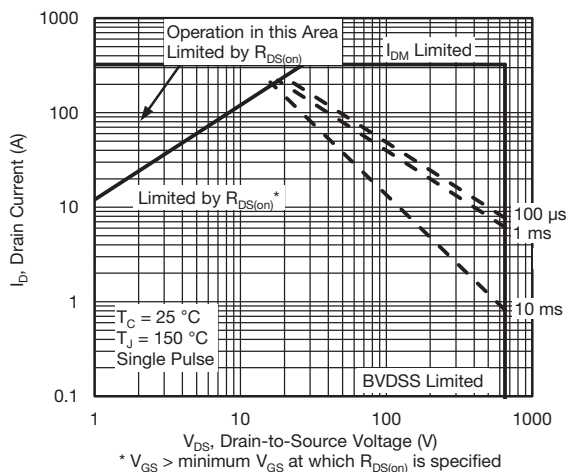
SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

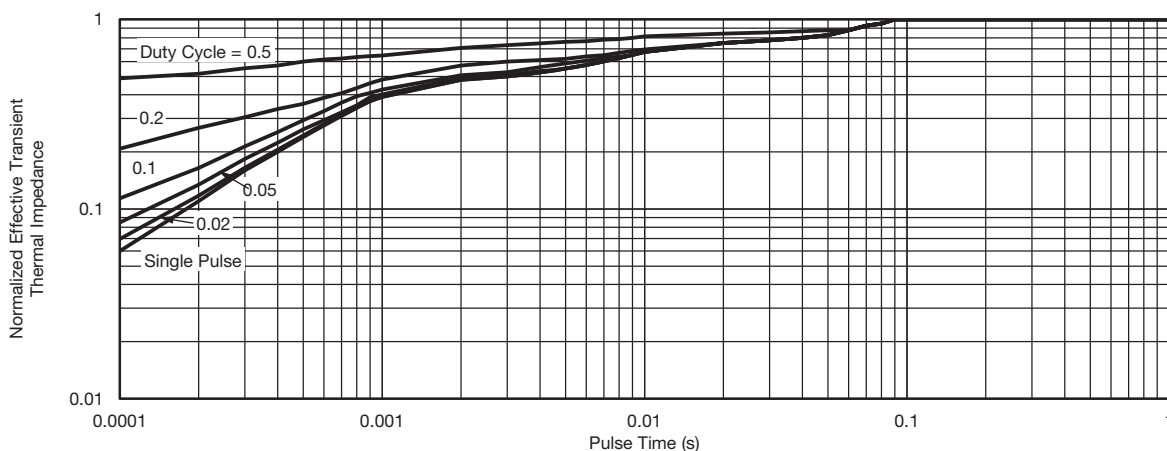
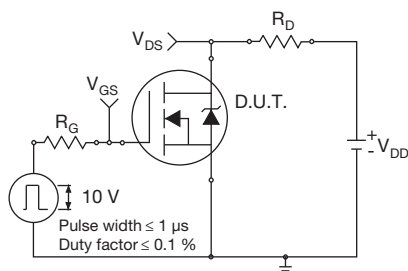
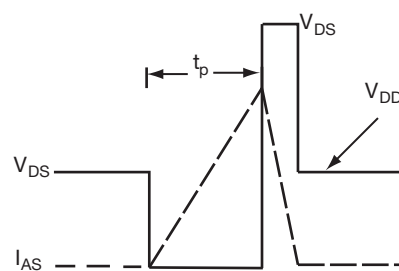
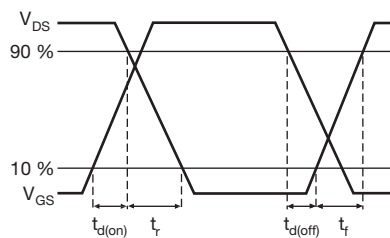
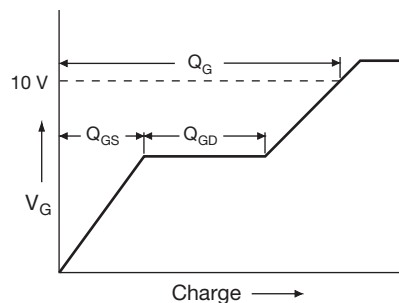
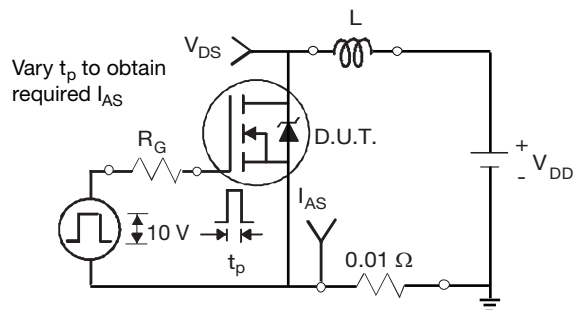
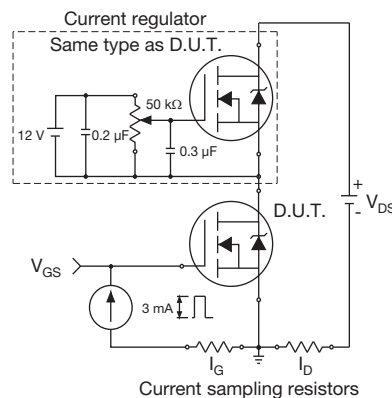
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		650	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.83	-	V/°C
Gate Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
		V _{GS} = ± 30 V		-	-	± 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 520 V, V _{GS} = 0 V, T _J = 125 °C		-	-	25	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 45 A	-	0.025	0.029	Ω
Forward Transconductance ^a	g _{fs}	V _{DS} = 30 V, I _D = 45 A		-	32	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 300 kHz		-	11 826	-	pF
Output Capacitance	C _{oss}			-	528	-	
Reverse Transfer Capacitance	C _{rss}			-	9	-	
Effective Output Capacitance, Energy Related ^a	C _{o(er)}	V _{GS} = 0 V, V _{DS} = 0 V to 520 V		-	384	-	pF
Effective Output Capacitance, Time Related ^b	C _{o(tr)}			-	1502	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 45 A, V _{DS} = 520 V	-	394	591	nC
Gate-Source Charge	Q _{gs}			-	84	-	
Gate-Drain Charge	Q _{gd}			-	160	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 520 V, I _D = 45 A, V _{GS} = 10 V, R _g = 9.1 Ω		-	85	128	ns
Rise Time	t _r			-	152	228	
Turn-Off Delay Time	t _{d(off)}			-	323	485	
Fall Time	t _f			-	267	401	
Gate Input Resistance	R _g	f = 1 MHz, open drain		0.6	1.2	2.4	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	87	A
Pulsed Diode Forward Current	I _{SM}			-	-	323	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 45 A, V _{GS} = 0 V		-	0.9	1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 45 A, dI/dt = 100 A/μs, V _R = 25 V		-	971	1942	ns
Reverse Recovery Charge	Q _{rr}			-	26	52	μC
Reverse Recovery Current	I _{RRM}			-	42	-	A

Notes

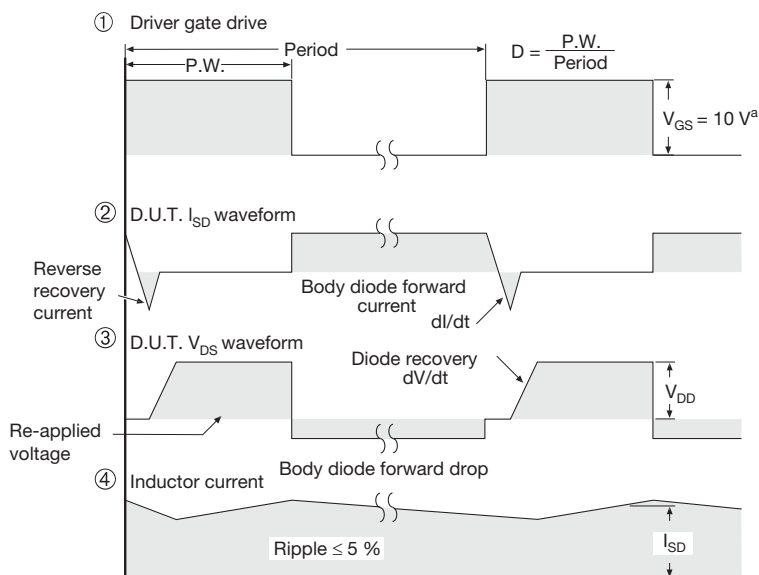
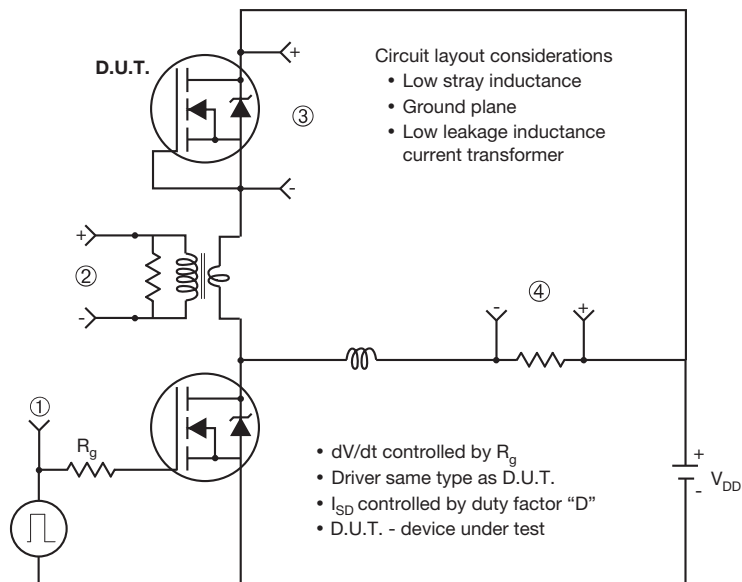
- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 10 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Typical Source-Drain Diode Forward Voltage

Fig. 11 - Temperature vs. Drain-to-Source Voltage

Fig. 9 - Maximum Safe Operating Area


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

Fig. 13 - Switching Time Test Circuit

Fig. 16 - Unclamped Inductive Waveforms

Fig. 14 - Switching Time Waveforms

Fig. 17 - Basic Gate Charge Waveform

Fig. 15 - Unclamped Inductive Test Circuit

Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 19 - For N-Channel

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